

CZT953

**SURFACE MOUNT
HIGH CURRENT
PNP SILICON TRANSISTOR**



SOT-223 CASE



www.centralemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT953 type is a high current PNP silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high voltage and high current amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation (Note 1)
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_{CBO} 140
 V_{CEO} 100
 V_{EBO} 6.0
 I_C 5.0
 P_D 3.0
 T_J, T_{stg} -65 to +150
 Θ_{JA} 41.7

UNITS

V
V
V
A
W
 $^{\circ}\text{C}$
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CBO}	$V_{CB}=100\text{V}$			50	nA
I_{CBO}	$V_{CB}=100\text{V}, T_A=100^{\circ}\text{C}$			1.0	μA
I_{CER}	$V_{CE}=100\text{V}, R_{BE}\leq 1.0\text{k}\Omega$			50	nA
I_{EBO}	$V_{EB}=6.0\text{V}$			10	nA
BV_{CBO}	$I_C=100\mu\text{A}$	140	170		V
BV_{CER}	$I_C=10\text{mA}, R_{BE}\leq 1.0\text{k}\Omega$	140	150		V
BV_{CEO}	$I_C=1.0\text{mA}$ (Note 2)	100	120	140	V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0	9.0		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		20	50	mV
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		90	120	mV
$V_{CE(SAT)}$	$I_C=2.0\text{A}, I_B=200\text{mA}$		170	220	mV
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=400\text{mA}$		320	420	mV
$V_{BE(SAT)}$	$I_C=4.0\text{A}, I_B=400\text{mA}$		1.0	1.2	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{mA}$	100			
h_{FE}	$V_{CE}=1.0\text{V}, I_C=1.0\text{A}$	100	200	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=3.0\text{A}$	50	70		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=4.0\text{A}$	30	45		
h_{FE}	$V_{CE}=1.0\text{V}, I_C=10\text{A}$		15		
f_T	$V_{CE}=10\text{V}, I_C=100\text{mA}, f=50\text{MHz}$		150		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		45		pF

Notes: (1) FR-4 Epoxy PC Board with copper mounting pad area of 4in^2 (minimum)
(2) Pulse Test: Pulse Width = $100\mu\text{s}$

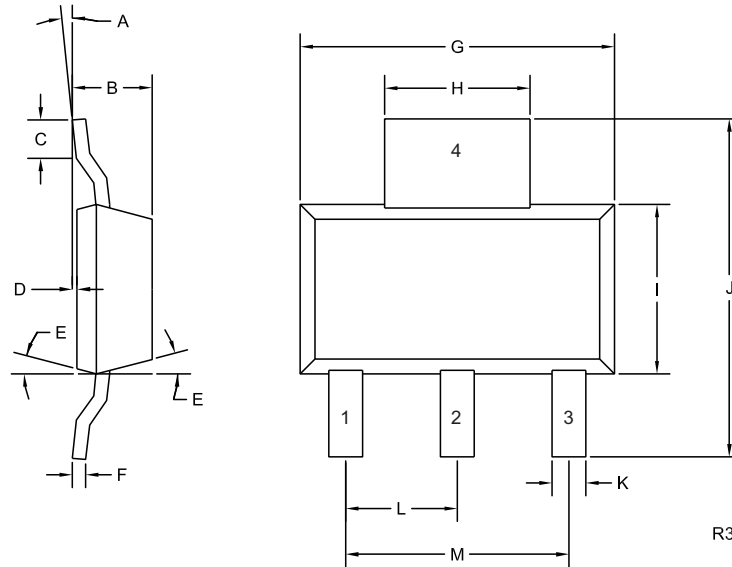
R4 (6-December 2012)

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SOT-223 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Base
- 2) Collector
- 3) Emitter
- 4) Collector

MARKING:

FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	10°	0°	10°
B	0.059	0.071	1.50	1.80
C	0.018	—	0.45	—
D	0.000	0.004	0.00	0.10
E	15°		15°	
F	0.009	0.014	0.23	0.35
G	0.248	0.264	6.30	6.70
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.70
J	0.264	0.287	6.70	7.30
K	0.024	0.033	0.60	0.85
L	0.091		2.30	
M	0.181		4.60	

SOT-223 (REV: R3)

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